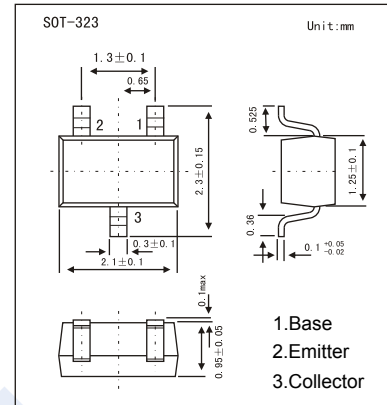


PNP Transistors

2SA1745

■ Features

- Low collector-to-emitter saturation voltage.
- Complementary to 2SC4555



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-20	V
Collector - Emitter Voltage	V _{CEO}	-15	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-0.5	A
Collector Current - Pulse	I _{CP}	-1	
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 uA, I _E =0	-20			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} = ∞	-15			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 uA, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -15 V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-5 mA, I _B =-0.5 mA		-15	-35	mV
		I _C =-200 mA, I _B =-10 mA		-200	-360	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-200 mA, I _B =-10 mA		-0.95	-1.2	V
DC current gain	h _{FE(1)}	V _{CE} = -2V, I _C = -10 mA	135		600	
	h _{FE(2)}	V _{CE} = -2V, I _C = -400 mA	70			
Collector output capacitance	C _{ob}	V _{CB} = -10V, f=1MHz		6.5		pF
Transition frequency	f _T	V _{CE} = -2V, I _C = -50 mA		400		MHz

■ Classification of h_{FE(1)}

Type	2SA1745-ES3	2SA1745-ES4	2SA1745-ES5
Range	135-270	200-400	300-600
Marking	ES3	ES4	ES5

PNP Transistors

2SA1745

Typical Characteristics

